

NGTB40N65IHRTG

IGBT with Monolithic Reverse Conducting Diode

This Insulated Gate Bipolar Transistor (IGBT) features robust and cost effective Field Stop (FS2) trench construction with a monolithic RC Diode. It provides a cost effective Solution for applications where diode losses are minimal. The IGBT is optimized for low conduction losses (low V_{CEsat}) and is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Conduction Design for Soft Switching Application
- Reduced Power Dissipation in Inducting Heating Application
- Reliable and Cost Effective Single Die Solution
- This is a Pb-Free Device

Typical Applications

- Inductive Heating
- Air Conditioning PFC
- Welding

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	650	V
Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_C	80 40	A
Pulsed collector current, T_{pulse} limited by T_{Jmax} , 10 μs pulse, $V_{GE} = 15\text{ V}$	I_{CM}	160	A
Diode forward current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_F	80 40	A
Diode pulsed current, T_{pulse} limited by T_{Jmax} , 10 μs pulse, $V_{GE} = 0\text{ V}$	I_{FM}	160	A
Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	P_D	405 202	W
Operating junction temperature range	T_J	-40 to +175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +175	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



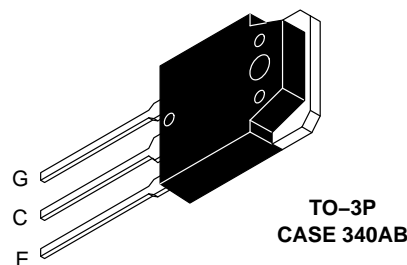
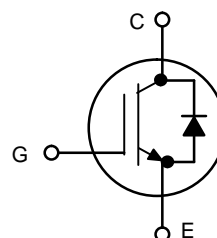
ON Semiconductor®

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40 A, 650 V

$V_{CEsat} = 1.55\text{ V}$

$E_{off} = 0.42\text{ mJ}$



MARKING DIAGRAM



40N65H = Specific Device Code
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NGTB40N65IHRTG	TO-3P (Pb-Free)	30 Units / Rail

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THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case	$R_{\theta JC}$	0.37	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	650	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^{\circ}\text{C}$	V_{CEsat}	–	1.55 1.95	1.7 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$	I_{CES}	–	– 1.0	0.3 –	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	100	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	4628	–	pF
Output capacitance		C_{oes}	–	148	–	
Reverse transfer capacitance		C_{res}	–	126	–	
Gate charge total	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	190	–	nC
Gate to emitter charge		Q_{ge}	–	38	–	
Gate to collector charge		Q_{gc}	–	90	–	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-off delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	–	197	–	ns
Fall time		t_f	–	74	–	
Turn-off switching loss		E_{off}	–	0.42	–	
Turn-off delay time	$T_J = 175^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(off)}$	–	210	–	ns
Fall time		t_f	–	106	–	
Turn-off switching loss		E_{off}	–	0.7	–	

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 40\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 40\text{ A}, T_J = 175^{\circ}\text{C}$	V_F	–	1.50 1.70	1.80 –	V
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

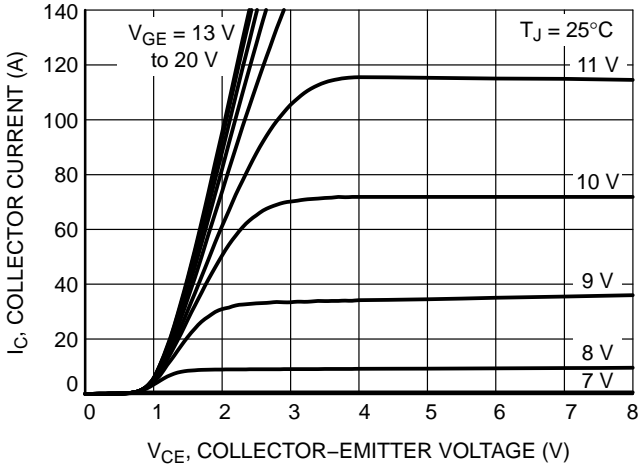


Figure 1. Output Characteristics

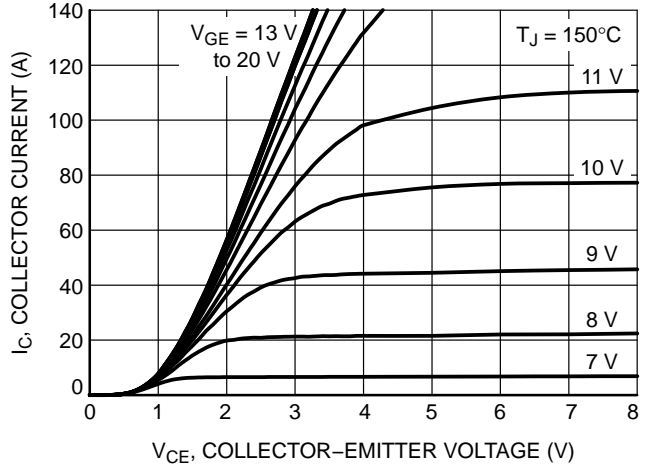


Figure 2. Output Characteristics

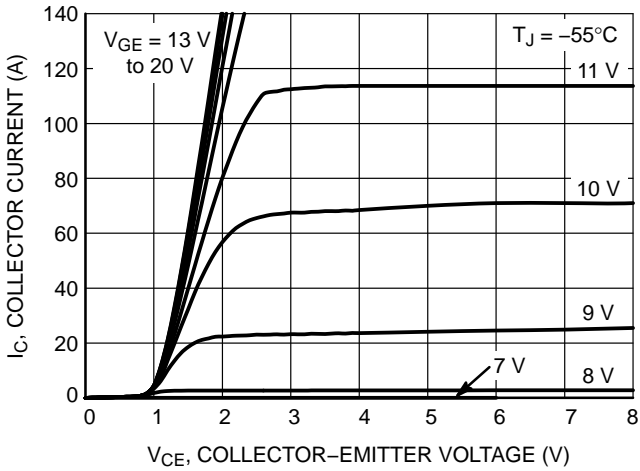


Figure 3. Output Characteristics

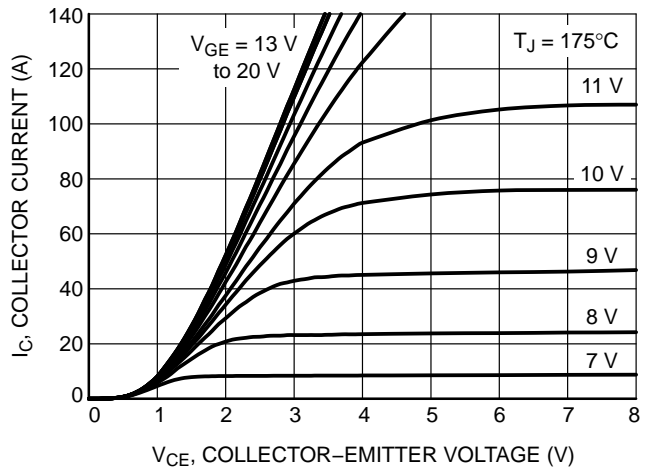


Figure 4. Output Characteristics

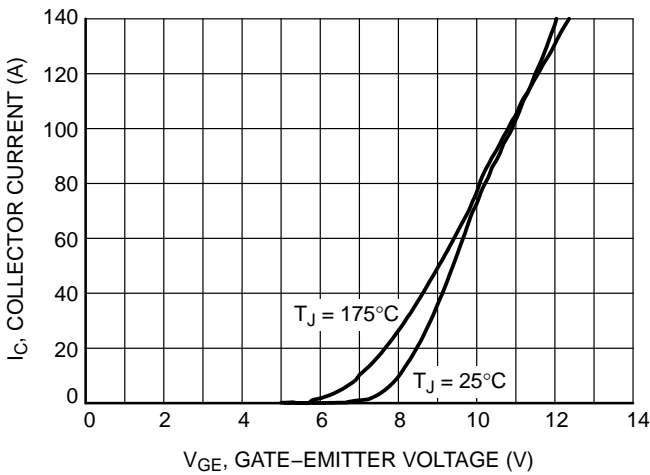


Figure 5. Typical Transfer Characteristics

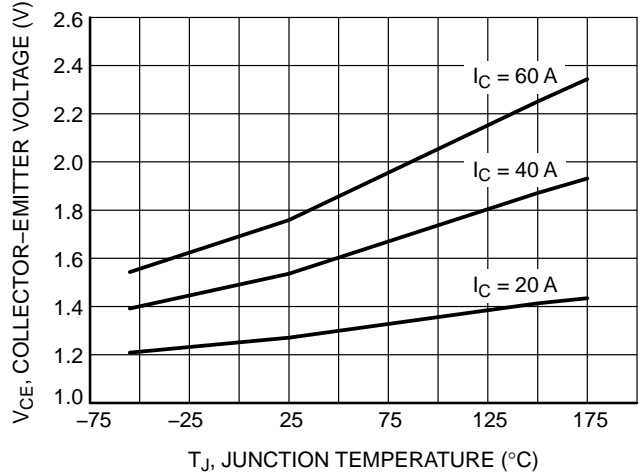


Figure 6. $V_{CE(sat)}$ vs. T_J

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TYPICAL CHARACTERISTICS

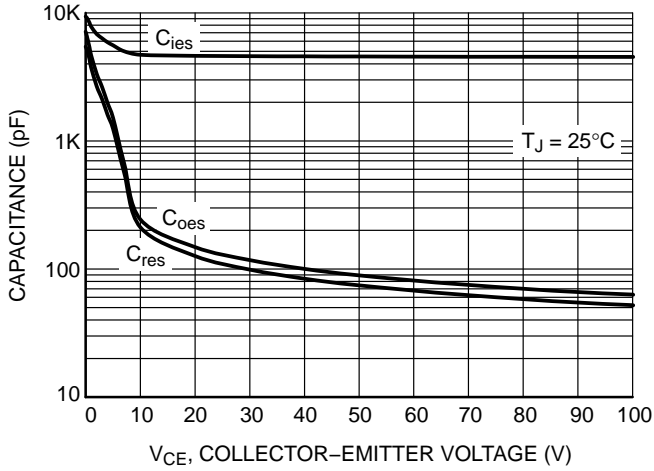


Figure 7. Typical Capacitance

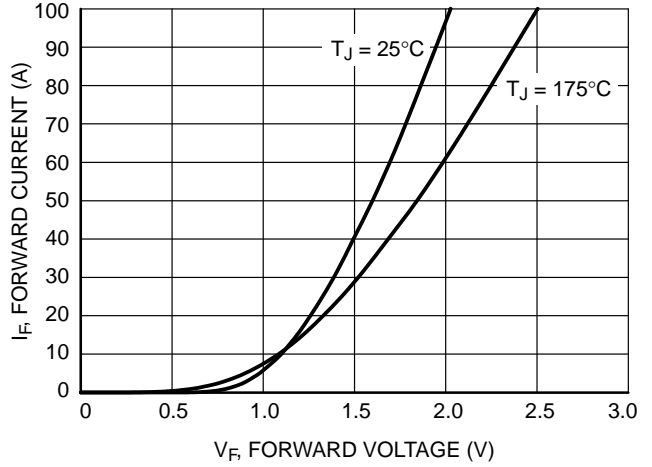


Figure 8. Diode Forward Characteristics

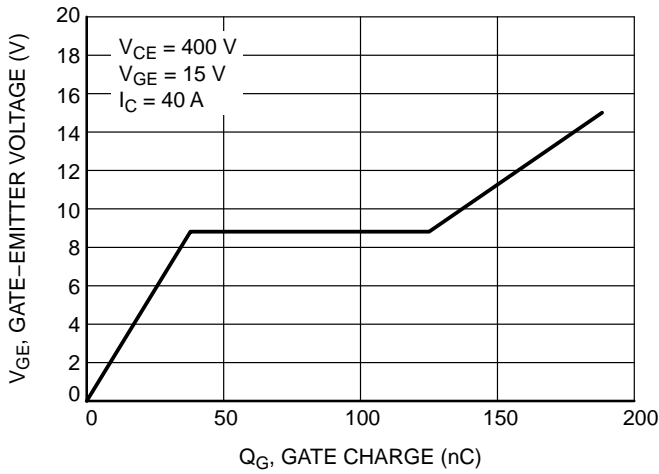


Figure 9. Typical Gate Charge

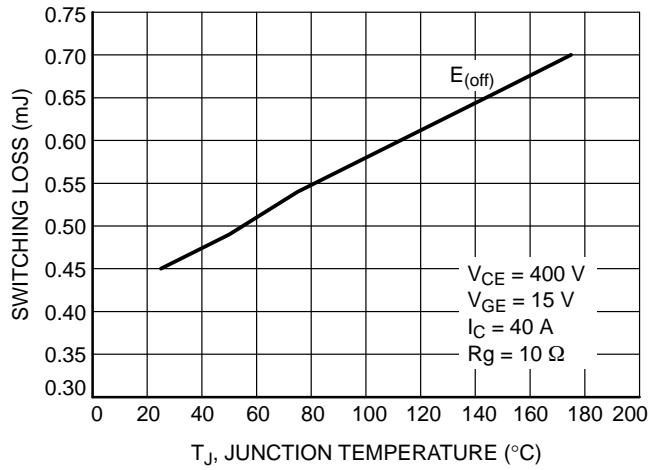


Figure 10. Switching Loss vs. Temperature

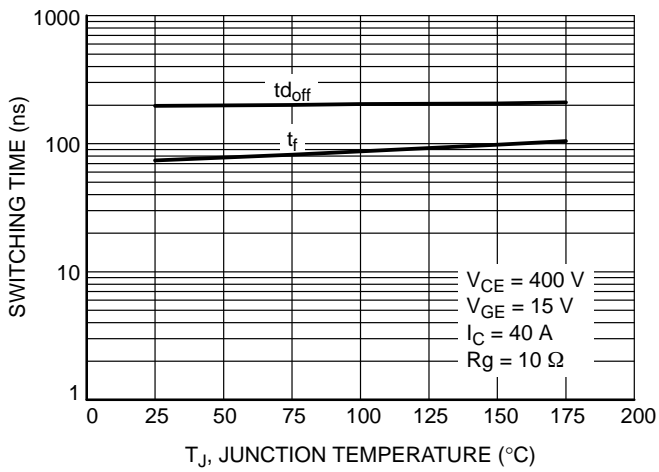


Figure 11. Switching Time vs. Temperature

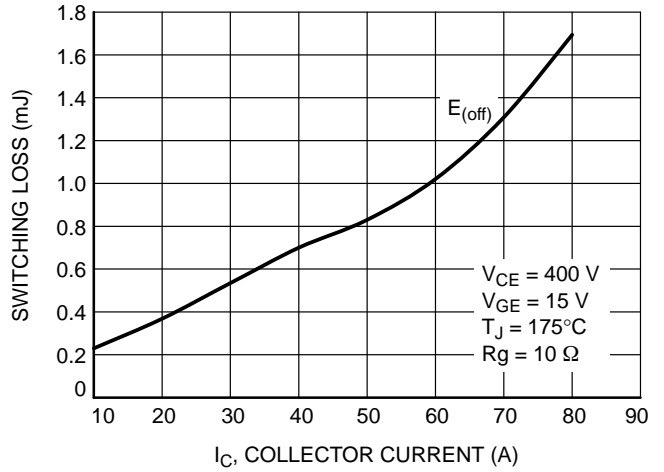


Figure 12. Switching Loss vs. I_C

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TYPICAL CHARACTERISTICS

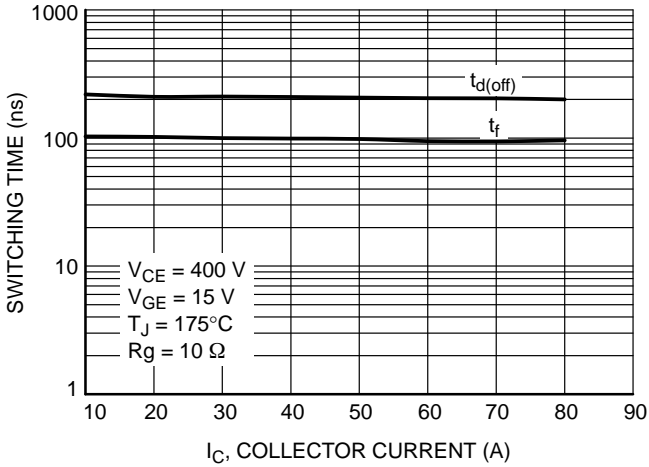


Figure 13. Switching Time vs. I_C

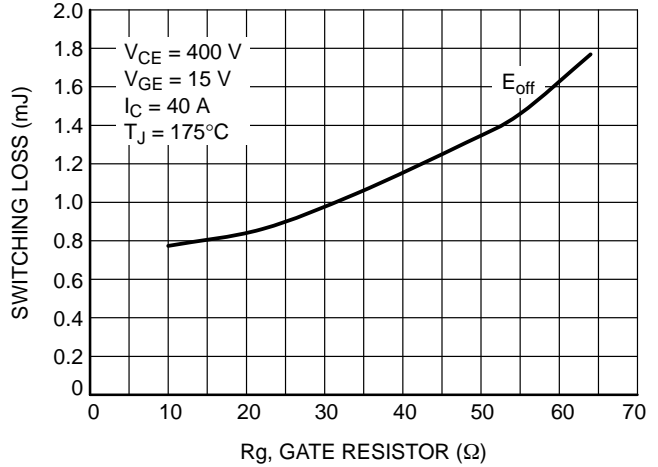


Figure 14. Switching Loss vs. R_g

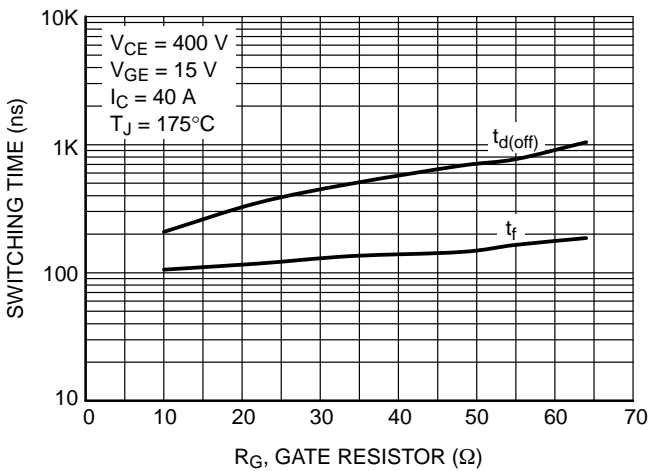


Figure 15. Switching Time vs. R_g

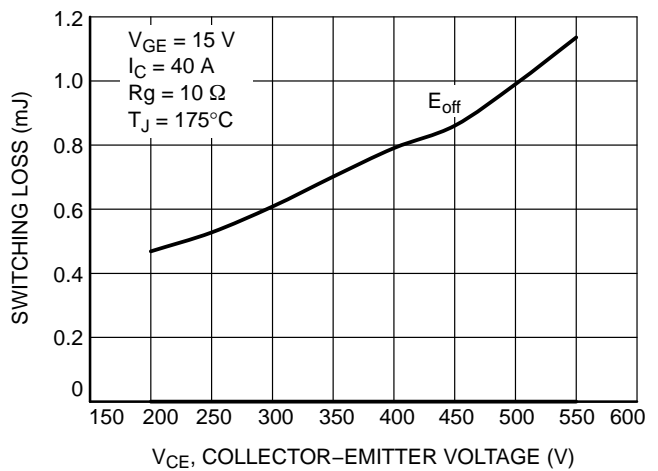


Figure 16. Switching Loss vs. V_{CE}

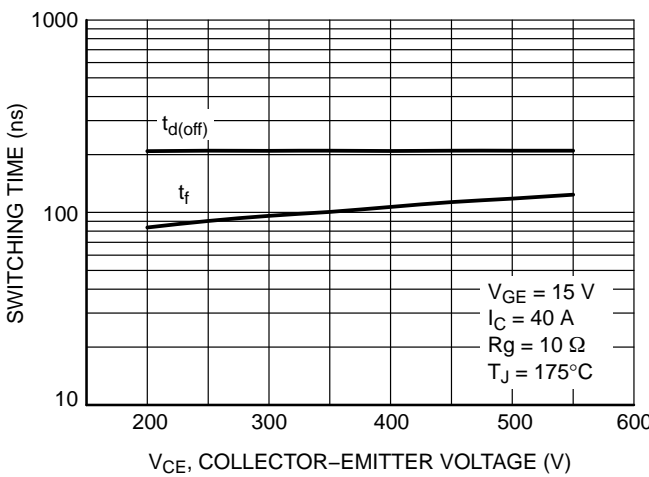


Figure 17. Switching Time vs. V_{CE}

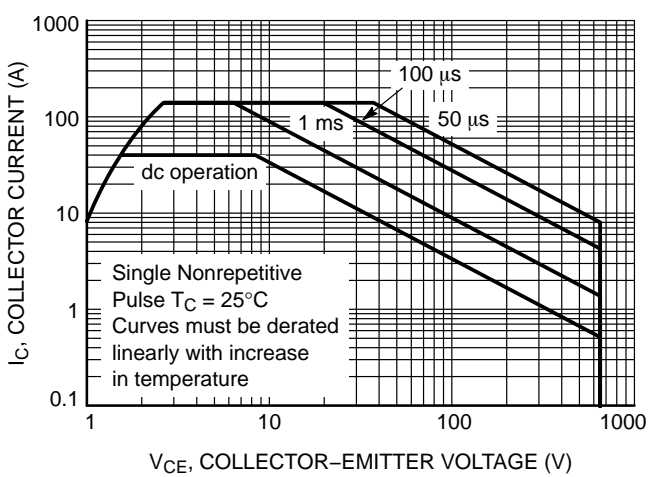


Figure 18. Safe Operating Area

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TYPICAL CHARACTERISTICS

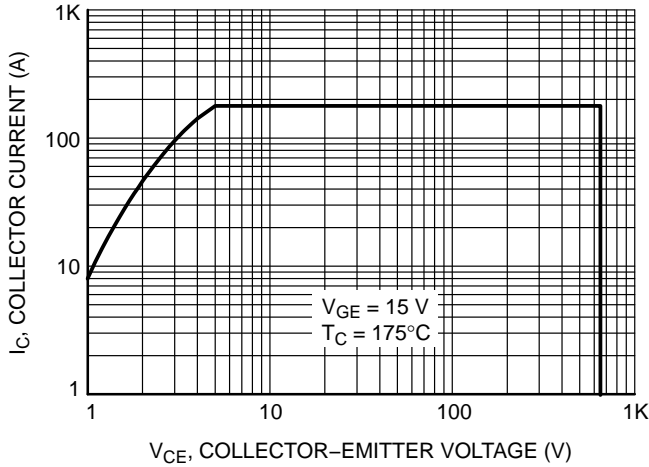


Figure 19. Reverse Bias Safe Operating Area

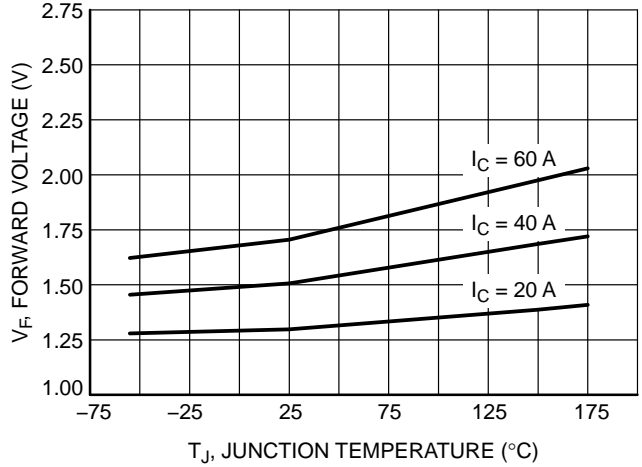


Figure 20. Forward Voltage vs. Junction Temperature

NGTB40N65IHRTG IGBT die self-heating square-wave duty cycle transient thermal response

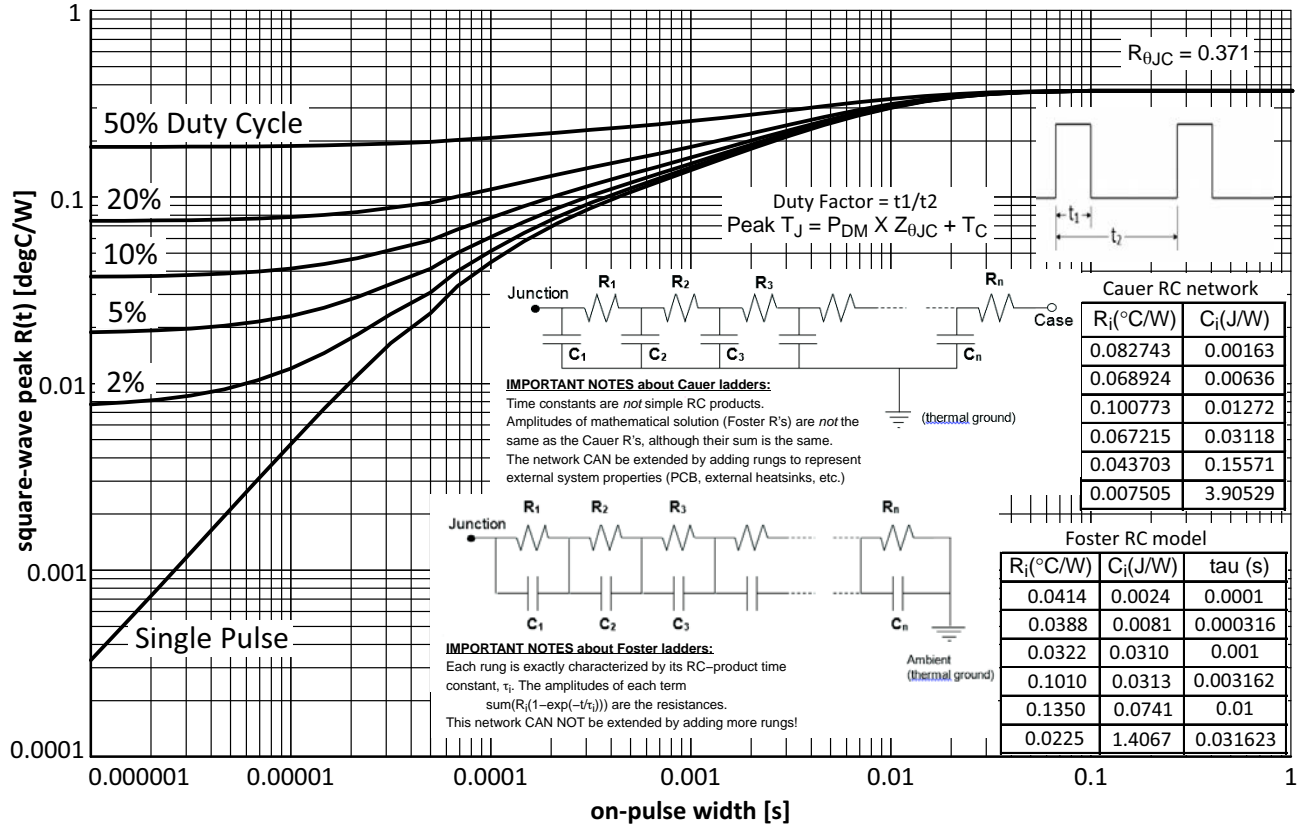


Figure 21. IGBT Transient Thermal Impedance

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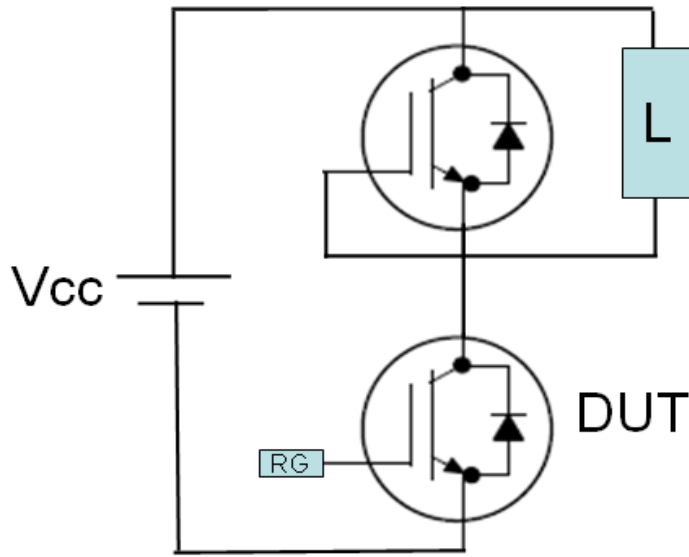


Figure 22. Test Circuit for Switching Characteristics

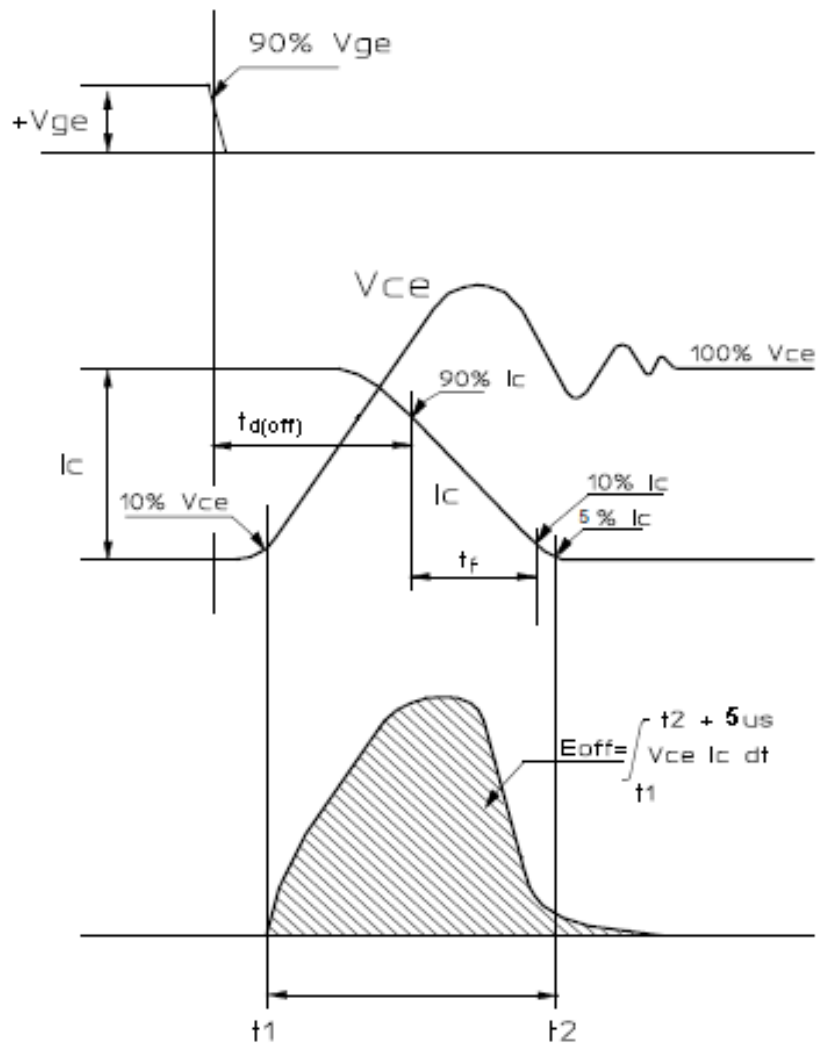
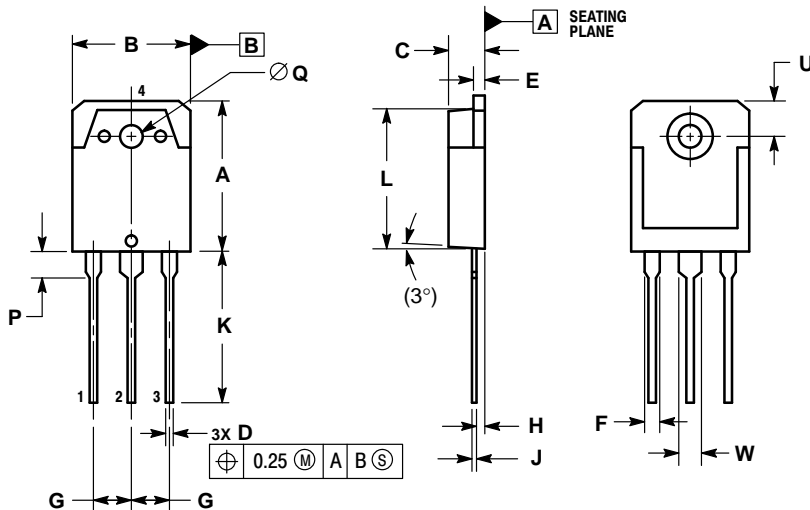


Figure 23. Definition of Turn Off Waveform

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PACKAGE DIMENSIONS

TO-3P-3LD
CASE 340AB-01
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
4. DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	19.70	19.90	20.10
B	15.40	15.60	15.80
C	4.60	4.80	5.00
D	0.80	1.00	1.20
E	1.45	1.50	1.65
F	1.80	2.00	2.20
G	5.45 BSC		
H	1.20	1.40	1.60
J	0.55	0.60	0.75
K	19.80	20.00	20.20
L	18.50	18.70	18.90
P	3.30	3.50	3.70
Q	3.10	3.20	3.50
U	5.00 REF		
W	2.80	3.00	3.20

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